



Express Mail No. EV 346 794 353 US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruno GHYSELEN et al.

Confirmation No.2491

Application No.: 10/784,017

Group Art Unit: 2822

Filing Date: February 20, 2004

Examiner: B.H. Au

For: METHOD FOR FORMING A RELAXED OR
PSEUDO-RELAXED USEFUL LAYER ON A
SUBSTRATE

Atty. Docket No.: 4717-10200

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Pursuant to applicants' duty of disclosure under 37 C.F.R. 1.56, enclosed are copies of four additional references for the Examiner's review and consideration. These references are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the PTO Form 1449.

The fee which is believed to be due for this submission is \$180. Please charge any and all fees for processing this statement and the amendment being filed concurrently herewith to **Winston & Strawn LLP** Deposit Account No. 50-1814.

Respectfully submitted,

Date

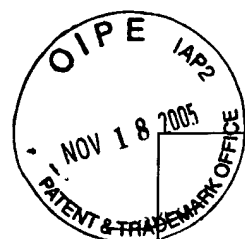
11/18/05

Allan A. Fanucci

(Reg. No. 30,256)

WINSTON & STRAWN LLP
Customer No. 28765

212-294-3311



LIST OF REFERENCES CITED BY APPLICANT
(Use several sheets if necessary)

ATTY. DOCKET NO.:

4717-10200

APPLICATION NO.:

10/784,017

APPLICANT:

Bruno GHYSELEN et al.

FILING DATE:

February 20, 2004

GROUP:

2822

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|----------------------|----|-----------------|--------|------------------|-------|----------|-------------------------------|
| | AA | 2003/0013305 A1 | 1/2003 | Sugii et al. | 438 | 689 | |
| | AB | 6,059,895 | 5/2000 | Chu et al. | 148 | 33.1 | |
| | AC | 6,100,166 | 8/2000 | Sakaguchi et al. | 438 | 455 | |
| | AD | | | | | | |
| | AE | | | | | | |
| | AF | | | | | | |
| | AG | | | | | | |
| | AI | | | | | | |

FOREIGN PATENT DOCUMENTS

| | | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION | |
|--|----|-----------------|--------|----------------|-------|----------|-------------|----|
| | | | | | | | YES | NO |
| | AJ | WO02/43153 | 5/2002 | PCT (Abstract) | | | X | |
| | AK | | | | | | | |
| | AL | | | | | | | |

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

| | | |
|--|----|--|
| | AM | |
| | AN | |
| | AO | |
| | AP | |
| | AQ | |

EXAMINER**DATE CONSIDERED**

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with **MPEP 609**; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

| | | | | | | | |
|---|----|--|---------|------------------------|-------|------------------|-------------------------------|
| LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i> | | | | ATTY. DOCKET NO.: | | APPLICATION NO.: | |
| | | | | 4717-10200 | | 10/784,017 | |
| | | | | APPLICANT: | | | |
| | | | | Bruno GHYSELEN et al. | | | |
| | | | | FILING DATE: | | GROUP: | |
| | | | | February 20, 2004 | | 2822 | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| *EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
| | AA | 5,461,243 | 10/1995 | Ek et al. | 257 | 190 | |
| | AB | 6,352,942 B1 | 3/2002 | Luan et al. | 438 | 770 | |
| | AC | 2002/0072130 | 6/2002 | Cheng et al. | 438 | 10 | |
| | AD | | | | | | |
| | AE | | | | | | |
| | AF | | | | | | |
| | AG | | | | | | |
| | AI | | | | | | |
| FOREIGN PATENT DOCUMENTS | | | | | | | |
| | | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION |
| | | | | | | | YES NO |
| | AJ | | | | | | |
| | AK | | | | | | |
| | AL | | | | | | |
| OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | |
| | AM | B. Holländer et al., "Strain relaxation of pseudomorphic Si _{1-x} Ge _x /Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication", Nuclear Instruments and Methods in Physics Research B 175-177 (2001) 357-367 (2001) | | | | | |
| | AN | K.D. Hobart et al. "Compliant Substrates: A Comparative Study of the Relaxation Mechanisms of Strained Films Bonded to High and Low Viscosity Oxides", Electronic Materials, Vol. 29, No. 7, pp. 897-900 (2000) | | | | | |
| | AO | Friedrich Schäffler, "High-mobility Si and Ge structures", Semicond. Sci. Technol., Vol. 12, pp.1515-1548 (1997) | | | | | |
| | AP | Q. Y. Tong et al "Extracts of "Semi-conductor on wafer bonding", Science and Technology, Interscience Technology, Wiley Interscience publication, Johnson Wiley & Sons, Inc. | | | | | |
| | AQ | J.P. Collinge, "Silicon-on-insulator technology", Materials to VLSI, 2nd Edition", Kluwer Academic Publisher, pp. 50-51. | | | | | |
| EXAMINER | | | | DATE CONSIDERED | | | |
| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | | |

| | | | | | | | |
|---|----|--|---------|------------------------|-------|------------------|-------------------------------|
| LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i> | | | | ATTY. DOCKET NO.: | | APPLICATION NO.: | |
| | | | | 4717-10200 | | 10/784,017 | |
| | | | | APPLICANT: | | | |
| | | | | Bruno GHYSELEN et al. | | | |
| | | | | FILING DATE: | | GROUP: | |
| | | | | February 20, 2004 | | 2822 | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| *EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
| | AA | 5,882,987 | 3/1999 | Sirikrishnan | 438 | 458 | |
| | AB | 5,906,951 | 5/1999 | Chu et al. | 438 | 751 | |
| | AC | 6,524,935 | 2/2003 | Canaperi et al. | 438 | 478 | |
| | AD | 6,573,126 B2 | 6/2003 | Cheng et al. | 438 | 149 | |
| | AE | 6,633,066 B1 | 10/2003 | Bae et al. | 257 | 347 | |
| | AF | 2003/0003679 A1 | 6/2003 | Doyle et al. | 438 | 406 | |
| | AG | 2003/0155568 A1 | 8/2003 | Cheng et al. | 257 | 12 | |
| | A1 | 2003/0168654 A1 | 9/2003 | Cheng et al. | 257 | 19 | |
| FOREIGN PATENT DOCUMENTS | | | | | | | |
| | | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION |
| | | | | | | | YES NO |
| | AJ | EP 1 248 294 A2 | 10/2002 | Europe | | | X |
| | AK | FR 2 818 010 (with English Abstract) | 8/2002 | France | | | X |
| | AL | DE 101 00 194 A1 | 6/2001 | Germany | | | X |
| | AM | WO 02/15244 A2 | 2/2002 | PCT | | | X |
| | AN | WO 02/47156 A1 | 2/2002 | PCT | | | X |
| | AO | WO 99/53539 | 10/1999 | PCT | | | X |
| OTHER REFERENCES <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i> | | | | | | | |
| | AP | T. Tezuka et al., XP001109835, High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique , Symposium On VLSI Tech., Digest of Technical Papers. Honolulu, NY:IEEE US, pp. 96-97 (2002) | | | | | |
| | AQ | S. Mantl et al., "Strain relaxation of epitaxial SGe layers on Si(100) improved by hydrogen implantation" Nuclear Instruments and Methods in Physics Research , Vol. 147, No. 1-4, pp. 29-34 (1999) | | | | | |
| EXAMINER | | | | DATE CONSIDERED | | | |
| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609 ; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | | |

AH